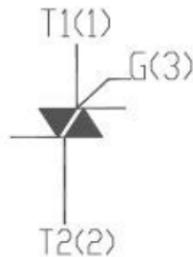




Features

- High current triac
- Low thermal resistance with clip bonding
- High commutation (4 quadrant) or very high commutation (3 quadrant) capability



VOLTAGE RANGE 600/800 Volts

CURRENT 8 Ampere



TO-220AB



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TO-252

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
VDRM VRRM	Repetitive Peak Off-State Voltage	BT137-600	600	V
		BT137-800	800	V
IT(RMS)	R.M.S On-State Current	T _c =110°C	8	A
ITSM	Surge On-State Current	tp=16.7ms/tp=10ms	80/84	A
I ² t	I ² t for fusing	Tp=10ms	30	A ² s
PG(AV)	Average Gate Power Dissipation	T _j =125°C	1	W
IGM	Peak Gate Current	T _j =125°C	4	A
T _j	Operating Junction Temperature		~40~125	°C
TSTG	Storage Temperature		~40~150	°C

BT137

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Value				Unit
			D	E	F	G	
IDRM	Repetitive Peak Off-State Current	T _J =25°C	≤5				μA
		T _J =125°C	≤1				mA
IRRM	Repetitive Peak Reverse Current	T _J =25°C	≤5				μA
		T _J =125°C	≤1				mA
VTM	Forward "on" voltage	I _T =12A t _p =380μs	≤1.55				V
VGT	Gate trigger voltage	V _D =12V ,R _L =30Ω	≤1.3				V
di/dt	Critical-rate of rise of commutation current.	I,II,III IV V _D =12V IGT==0.1A	≥50				A /us
			≥10				A /us
IGT	Gate trigger current	I,II,III IV V _D =12V R _L =30Ω	≤5	≤10	≤25	≤50	mA
			≤10	≤25	≤70	≤100	mA
IH	Holding current	I _T =0.2A	≤10	≤25	≤30	≤60	mA
VGD	Gate non-trigger voltage	ALL V _D =V _{DRM} T _J =125°C,R _L =3.3KΩ	≥0.2				V
dv/dt	Critical-rate of rise of commutation voltage	T _J =125°C V _D =2/3V _{DRM} Gate	≥5	≥10	≥50	≥200	V/us

RATING AND CHARACTERISTIC CURVES (BT137)

FIG.1: Maximum power dissipation versus RMS on-state current

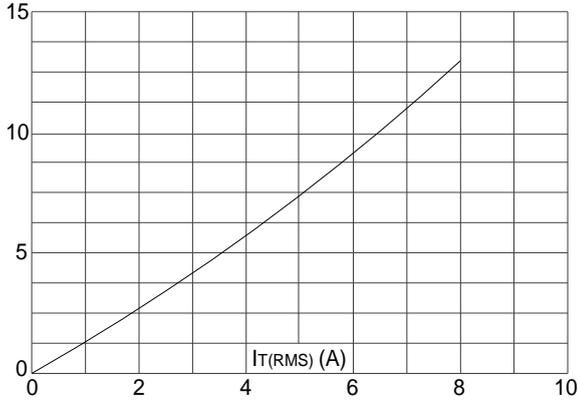


FIG.2: RMS on-state current versus case temperature

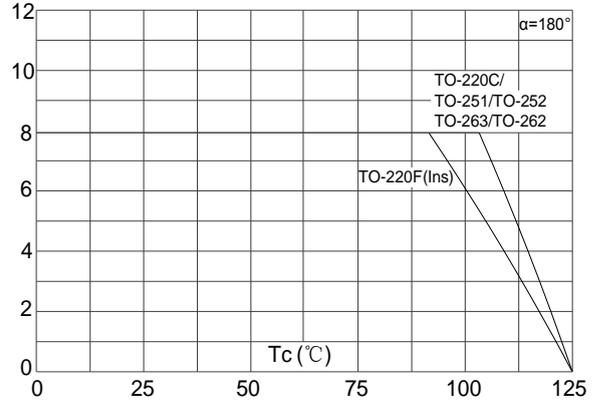


FIG.3: Surge peak on-state current versus number of cycles

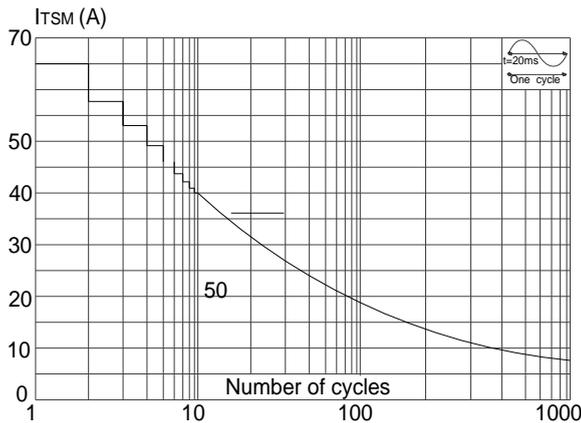


FIG.4: On-state characteristics (maximum values)

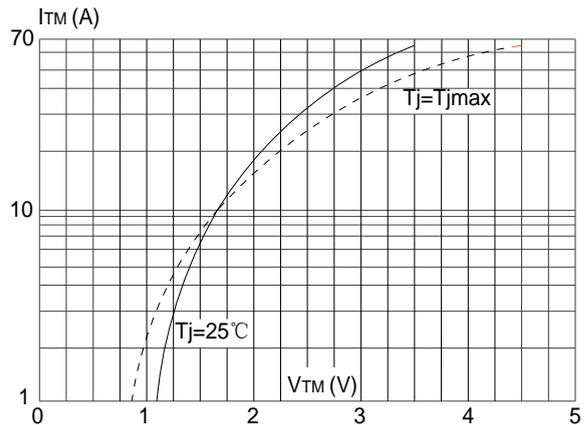


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

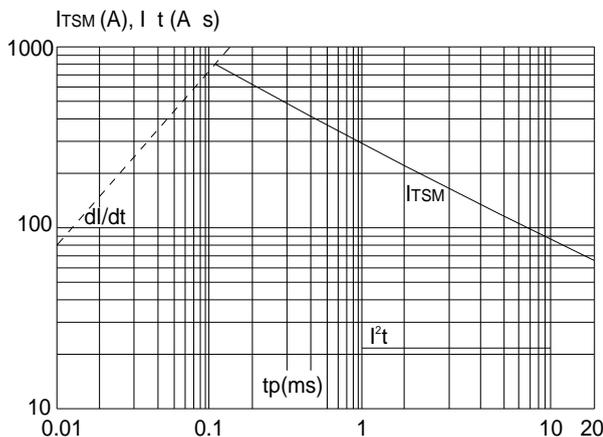
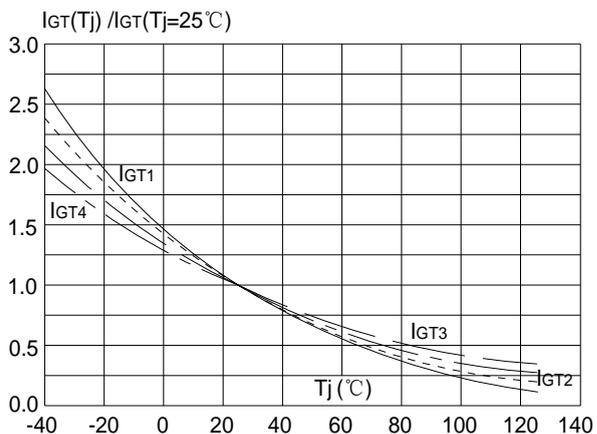


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



RATING AND CHARACTERISTIC CURVES (BT137)

FIG.7: Relative variations of holding current versus junction temperature

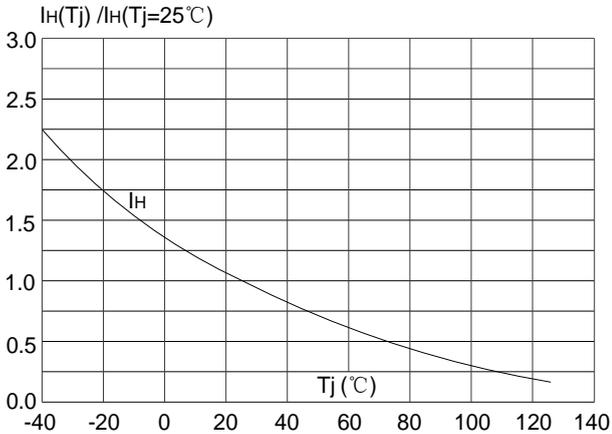
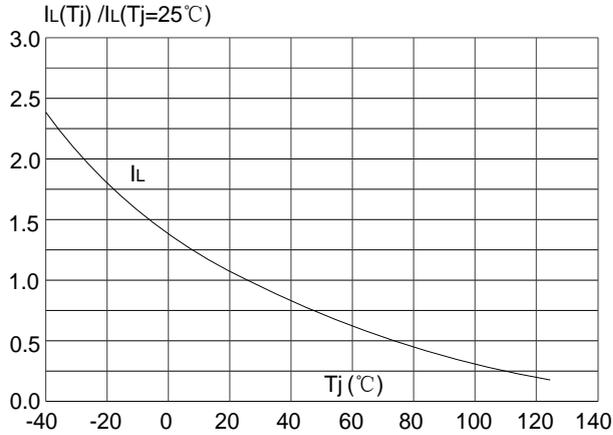
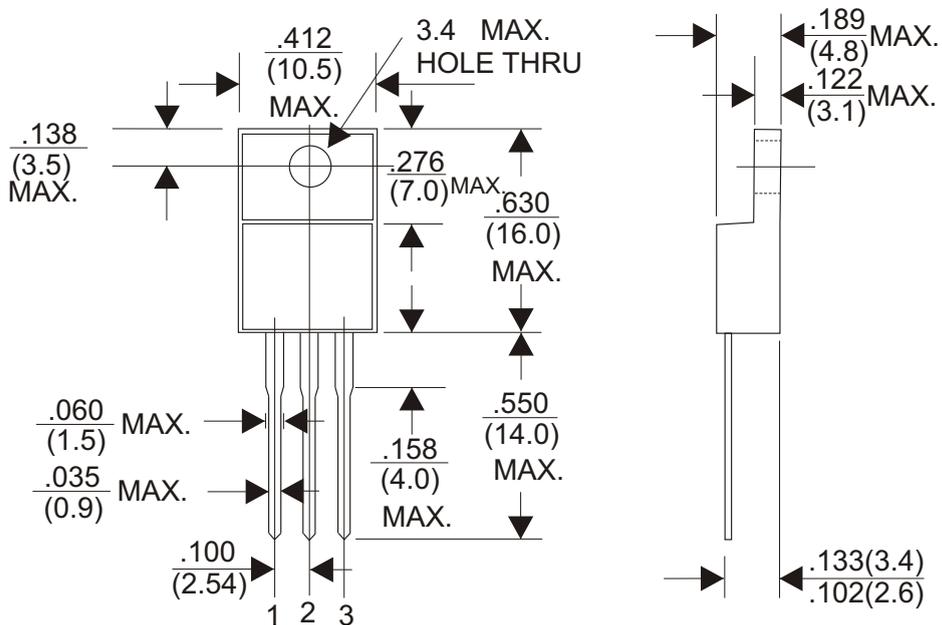


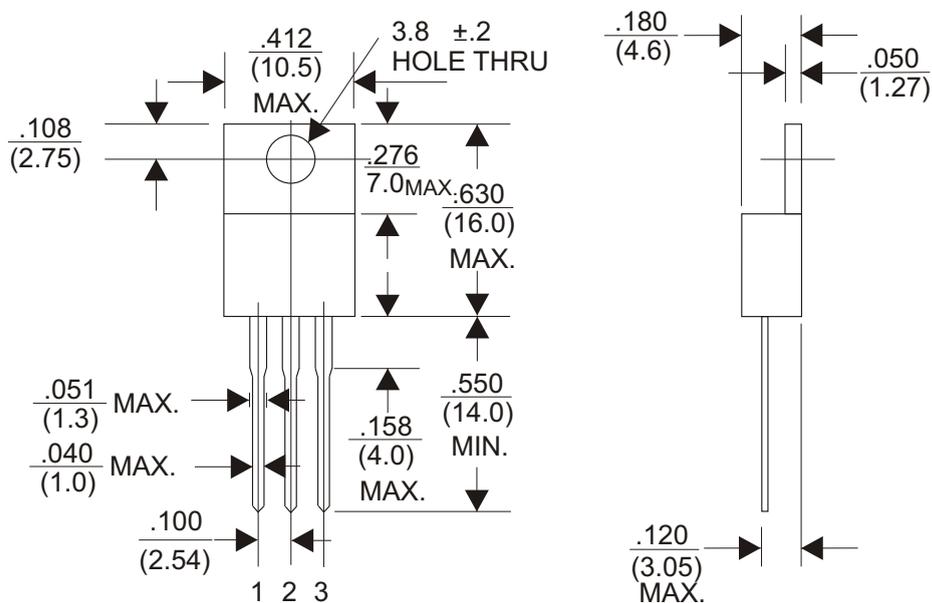
FIG.8: Relative variations of latching current versus junction temperature



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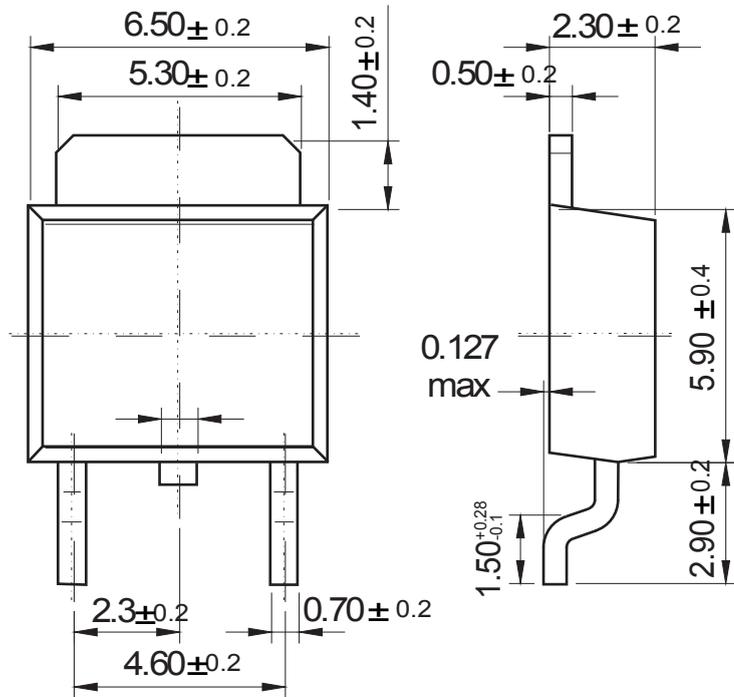


TO-220AB



TO-252

Unit: mm



Dimensions in inches and (millimeters)